



**CHENMKO ENTERPRISE CO.,LTD**

**SURFACE MOUNT  
SWITCHING DIODE**

**VOLTAGE 80 Volts CURRENT 100 mAmpere**

**CHN10PT**

*Lead free devices*

**APPLICATION**

- \* Ultra high speed switching

**FEATURE**

- \* Small surface mounting type. (SC-74/SOT-457)
- \* Multiple diodes in one small surface mount package.
- \* Suitable for high packing density.
- \* Maximum total power dissipation is 300mW.
- \* Peak forward current is 300mA.

**CONSTRUCTION**

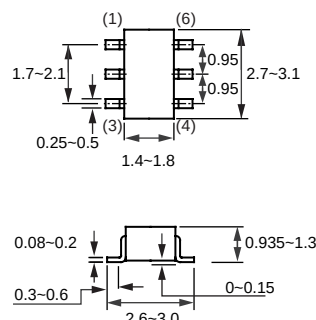
- \* Silicon epitaxial planar

**MARKING**

- \* D1P



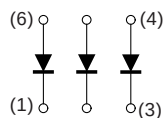
**SC-74/SOT-457**



Dimensions in millimeters

**SC-74/SOT-457**

**CIRCUIT**



**MAXIMUM RATINGS** ( At TA = 25°C unless otherwise noted )

| RATINGS                                                | SYMBOL | CHN10PT     | UNITS |
|--------------------------------------------------------|--------|-------------|-------|
| Maximum Recurrent Peak Reverse Voltage                 | VRRM   | 80          | Volts |
| Maximum RMS Voltage                                    | VRMS   | 56          | Volts |
| Maximum DC Blocking Voltage                            | VDC    | 80          | Volts |
| Maximum Average Forward Rectified Current              | IO     | 100         | mAmps |
| Peak Forward Surge Current at 1uSec.                   | IFSM   | 4.0         | Amps  |
| Typical Junction Capacitance between Terminal (Note 1) | CJ     | 3.5         | pF    |
| Maximum Reverse Recovery Time (Note 2)                 | TRR    | 4.0         | nSec  |
| Maximum Operating Temperature Range                    | TJ     | +150        | °C    |
| Storage Temperature Range                              | TSTG   | -55 to +150 | °C    |

**ELECTRICAL CHARACTERISTICS** ( At TA = 25°C unless otherwise noted )

| CHARACTERISTICS                                    | SYMBOL | CHN10PT | UNITS |
|----------------------------------------------------|--------|---------|-------|
| Maximum Instantaneous Forward Voltage at IF= 100mA | VF     | 1.20    | Volts |
| Maximum Average Reverse Current at VR= 70V         | IR     | 0.1     | uAmps |

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 6.0 volts.  
2. Measured at applied forward current of 5mA and reverse voltage of 6.0 volts.  
3. ESD sensitive product handling required.

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## RATING CHARACTERISTIC CURVES ( CHN10PT )

FIG. 1 - POWER DERATING CURVE

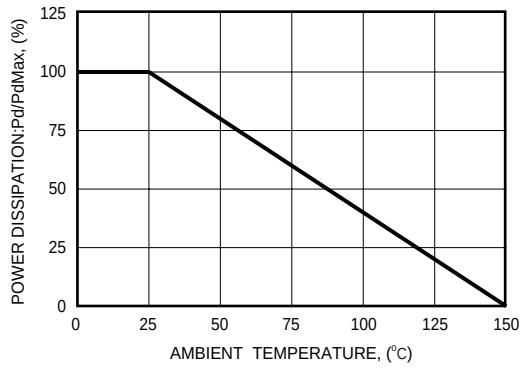


FIG. 2 - FORWARD CHARACTERISTICS

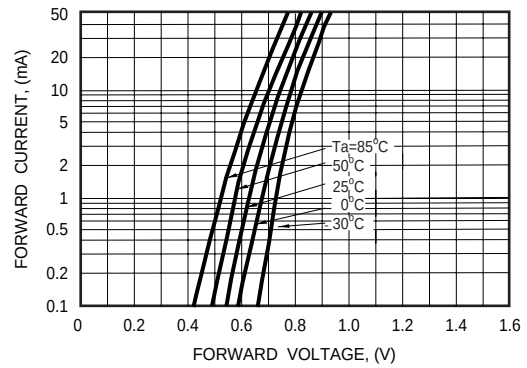


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

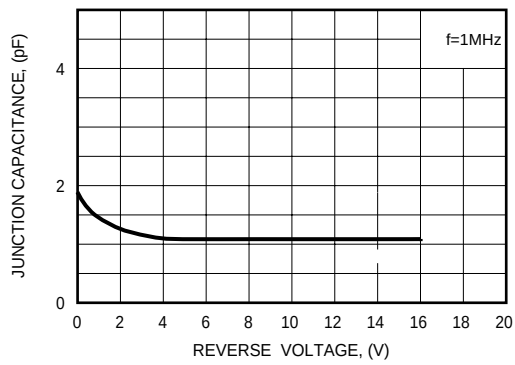


FIG. 4 - REVERSE CHARACTERISTICS

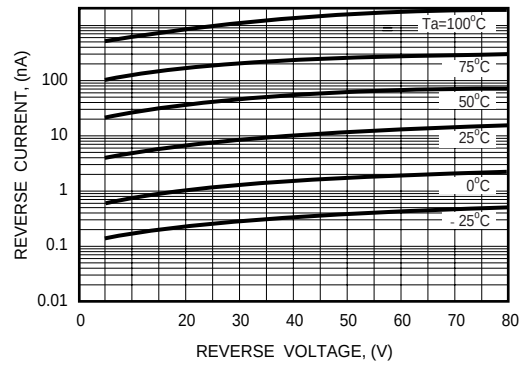


FIG. 5 - REVERSE RECOVERY TIME

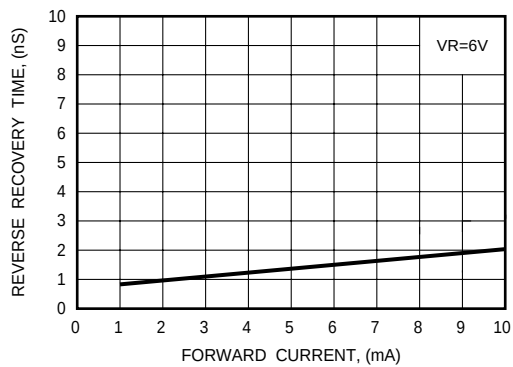


FIG. 6 - REVERSE RECOVERY TIME MEASUREMENT CIRCUIT

